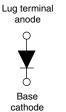
**Vishay Semiconductors** 

# High Performance Schottky Rectifier, 120 A



www.vishay.com

HALF-PAK (D-67)



PRIMARY CHARACTERISTICS			
I <sub>F(AV)</sub> 120 A			
V <sub>R</sub>	30 V		
Package	HALF-PAK (D-67)		
Circuit configuration	Single		

### **FEATURES**

- 150 °C T<sub>J</sub> operation
- Low forward voltage drop
- High frequency operation
- · Guard ring for enhanced ruggedness and long term reliability
- Designed and qualified for industrial level
- UL approved file E222165
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

### DESCRIPTION

The VS-122NQ.. high current Schottky rectifier module series has been optimized for low reverse leakage at high temperature. The proprietary barrier technology allows for reliable operation up to 175 °C junction temperature. Typical applications are in high current switching power supplies, plating power supplies, UPS systems, converters, freewheeling diodes, welding, and reverse battery protection.

MAJOR RATINGS AND CHARACTERISTICS					
SYMBOL	CHARACTERISTICS	CHARACTERISTICS VALUES			
I <sub>F(AV)</sub>	Rectangular waveform	120	A		
V <sub>RRM</sub>		30	V		
I <sub>FSM</sub>	t <sub>p</sub> = 5 μs sine	18 000	A		
V <sub>F</sub>	120 A <sub>pk</sub> , T <sub>J</sub> = 125 °C	0.47	V		
TJ	Range	-55 to +150	°C		

VOLTAGE RATINGS				
PARAMETER	SYMBOL	VS-122NQ030PbF	UNITS	
Maximum DC reverse voltage	V <sub>R</sub>	30	V	
Maximum working peak reverse voltage	V <sub>RWM</sub>	30	v	

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum average forward current See fig. 5	I <sub>F(AV)</sub>	50 % duty cycle at $T_C$ = 115 °C, rectangular waveform		120	А
Maximum peak one cycle non-repetitive surge current		5 µs sine or 3 µs rect. pulse	Following any rated load condition and with rated	18 000	A
See fig. 7	I <sub>FSM</sub>	10 ms sine or 6 ms rect. pulse	V <sub>RRM</sub> applied	2000	
Non-repetitive avalanche energy	E <sub>AS</sub>	T <sub>J</sub> = 25 °C, I <sub>AS</sub> = 11 A, L = 1 mH		54	mJ
Repetitive avalanche current	I <sub>AR</sub>	Current decaying linearly to zero in 1 $\mu$ s Frequency limited by T <sub>J</sub> maximum V <sub>A</sub> = 1.5 x V <sub>R</sub> typical		12	А

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ELECTRICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
	V <sub>FM</sub> <sup>(1)</sup>	120 A	T.I = 25 °C	0.57	V
Maximum forward voltage drop per leg		240 A	1j=25 0	0.75	
See fig. 1	VFM V	120 A	T.I = 125 °C	0.47	
		240 A	1j = 123 0	0.67	
Maximum reverse leakage current per leg	I <sub>RM</sub> <sup>(1)</sup>	T <sub>J</sub> = 25 °C	$V_{\rm B}$ = Rated $V_{\rm B}$	10	mA
See fig. 2			VR - naleu VR	560	ША
Maximum junction capacitance	CT	$V_R = 5 V_{DC}$ (test signal range 100 kHz to 1 MHz) 25 °C 7		7400	pF
Typical series inductance	L <sub>S</sub>	From top of terminal hole to mounting plane 7.		7.0	nH
Maximum voltage rate of change	dV/dt	Rated V <sub>R</sub> 10 000		V/µs	

Note

 $^{(1)}\,$  Pulse width < 300  $\mu s,$  duty cycle < 2  $\,\%$ 

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum junction and storage te	mperature range	T <sub>J</sub> , T <sub>Stg</sub>		-55 to 150	°C	
Maximum thermal resistance, junction to case		R <sub>thJC</sub>	DC operation See fig. 4	0.38	°C/W	
Typical thermal resistance, case t	pical thermal resistance, case to heatsink R		Mounting surface, smooth and greased	0.05		
Approximate weight				30	g	
				1.06	oz.	
	minimum			3 (26.5)		
Mounting torque maximum			Non-lubric stand days and	4 (35.4)	N ⋅ m	
Terminal torque	minimum		Non-lubricated threads	3.4 (30)	(lbf · in)	
	maximum			5 (44.2)		
Case style	se style			HALF-PA	K module	

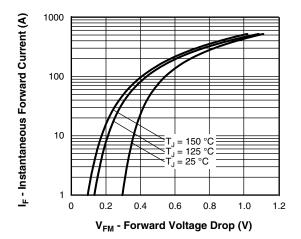


Fig. 1 - Maximum Forward Voltage Drop Characteristics

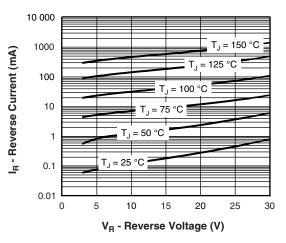


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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# VS-122NQ030PbF

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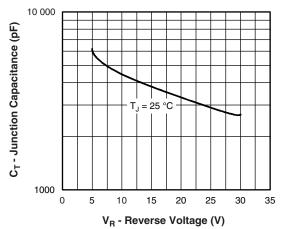


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

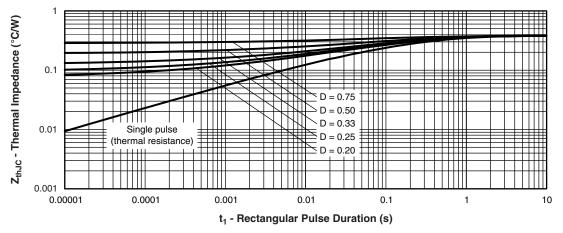
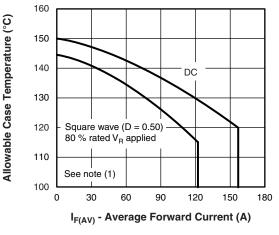
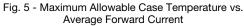


Fig. 4 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics





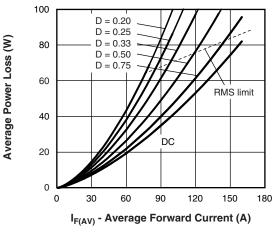


Fig. 6 - Forward Power Loss Characteristics

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# VS-122NQ030PbF

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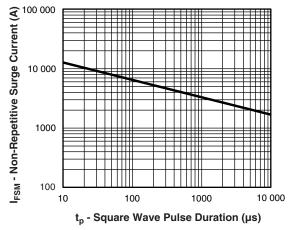


Fig. 7 - Maximum Non-Repetitive Surge Current

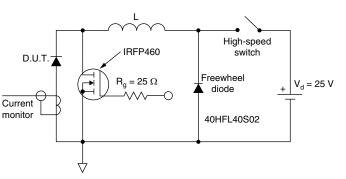
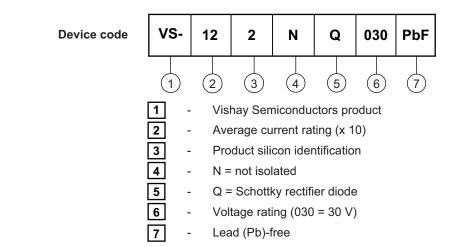


Fig. 8 - Unclamped Inductive Test Circuit

#### Note

 $Pd_{REV}$  = inverse power loss =  $V_{R1} \times I_R (1 - D)$ ;  $I_R$  at  $V_{R1}$  = rated  $V_R$ 

### **ORDERING INFORMATION TABLE**



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 $<sup>^{(1)} \</sup>mbox{ Formula used: } T_C = T_J - (Pd + Pd_{REV}) \ x \ R_{thJC}; \\ Pd = \mbox{ Forward power loss } = I_{F(AV)} \ x \ V_{FM} \ at \ (I_{F(AV)}/D) \ (see \ fig. \ 6);$ 

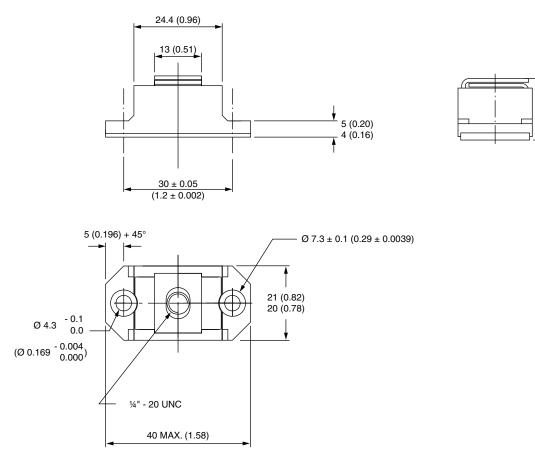
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17.5 (0.69) 16.5 (0.65)



### **DIMENSIONS** in millimeters (inches)

SHAY





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